

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A nitride semiconductor substrate comprising:
a group III nitride semiconductor substrate;
a mask formed over the group III nitride semiconductor substrate; and
a group III nitride semiconductor multilayer film formed above the mask,
wherein the group III nitride semiconductor substrate has a dislocation density in the a
vicinity of athe surface thereof of $1 \times 10^7/\text{cm}^2$ or less, and
the mask has a polycrystalline material deposited on athe surface thereof.
2. (original): The nitride semiconductor substrate according to Claim 1, wherein the
polycrystalline material is formed from a material containing aluminum and nitrogen as essential
elements.
3. (original): The nitride semiconductor substrate according to Claim 1, wherein voids
are formed on the surface of the mask having the polycrystalline material.
4. (original): The nitride semiconductor substrate according to Claim 1, wherein the
mask is provided on the surface of the group III nitride semiconductor substrate.
5. (canceled).

6. (currently amended): A nitride semiconductor device comprising:
a group III nitride semiconductor substrate;
a mask formed over the group III nitride semiconductor substrate; and
a group III nitride semiconductor multilayer film formed above the mask, the group III nitride semiconductor multilayer film including an active layer,
wherein the group III nitride semiconductor substrate has a dislocation density in ~~a~~the vicinity of ~~a~~the surface thereof of $1 \times 10^7/\text{cm}^2$ or less, and
the mask has a polycrystalline material deposited on ~~a~~the surface thereof.

7. (original): The nitride semiconductor device according to Claim 6, wherein the polycrystalline material is formed from a material containing aluminum and nitrogen as essential elements.

8. (original): The nitride semiconductor device according to Claim 6, wherein voids are formed on the surface of the mask having the polycrystalline material.

9. (original): The nitride semiconductor device according to Claim 6, wherein the mask is provided on the surface of the group III nitride semiconductor substrate.

10. (canceled).

11. (currently amended): The nitride semiconductor device according to Claim 6, wherein the mask is provided in ~~at~~the vicinity of a device separating groove of the nitride semiconductor device.

12-21. (canceled).